# PSMN7R2-100YSF

NextPower 100 V, 6.9 mOhm N-channel MOSFET in LFPAK56 package

16 March 2022

**Preliminary data sheet** 

# 1. General description

NextPower 100 V, standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial and consumer applications.

### 2. Features and benefits

- Low Q<sub>rr</sub> for higher efficiency and lower spiking
- Low Q<sub>G</sub> × R<sub>DSon</sub> FOM for high efficiency switching applications
- Strong avalanche energy rating (E<sub>AS</sub>)
- · Avalanche rated and 100% tested
- Ha-free and RoHS compliant LFPAK56 package
- · Wave-solderable LFPAK56 package

# 3. Applications

- Synchronous rectifier in AC-DC and DC-DC
- Primary side switch in 48 V DC-DC
- · BLDC motor control
- USB-PD and mobile fast-charge adapters
- Flyback and resonant topologies

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	111	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	194	W
Tj	junction temperature			-55	-	175	°C
Static characte	eristics		•	•		'	
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; Fig. 12		-	5	6.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ Fig. 13		-	7.8	11	mΩ
Dynamic chara	cteristics						
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V;		3.2	11	25	nC
Q <sub>G(tot)</sub>	total gate charge	T <sub>j</sub> = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>		25.4	51	76	nC
Avalanche rug	gedness			•			
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 38 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 70 μs; Fig. 4	[1]	-	-	173	mJ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain d	Source-drain diode						
Q <sub>r</sub>		$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 50 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; Fig. 18		-	21	-	nC

<sup>[1]</sup> Protected by 100% test

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source		D
3	S	source		
4	G	gate	0 0 0 0	G_( = ]
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	mbb076 S

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package		
	Name	Description	Version
PSMN7R2-100YSF	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

# 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	100	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	194	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	111	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	-	78	Α
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; <u>Fig. 3</u>	-	443	Α
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drai	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	111	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$	-	443	Α

PSMN7R2-100YSF

Symbol	Parameter	Conditions		Min	Max	Unit	
Avalanche ruggedness							
	non-repetitive drain- source avalanche energy	$I_D$ = 38 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 70 μs; Fig. 4	[1]	-	173	mJ	
I <sub>AS</sub>		$V_{sup} = 100 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; Fig. 4$	[1]	-	38	А	

#### [1] Protected by 100% test

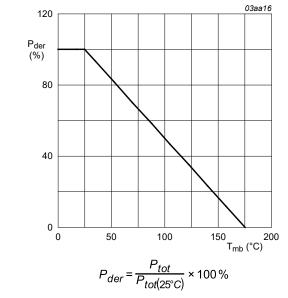


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

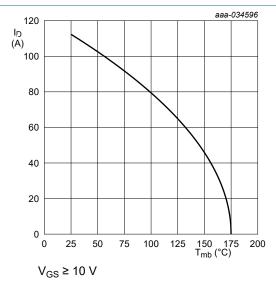


Fig. 2. Continuous drain current as a function of mounting base temperature

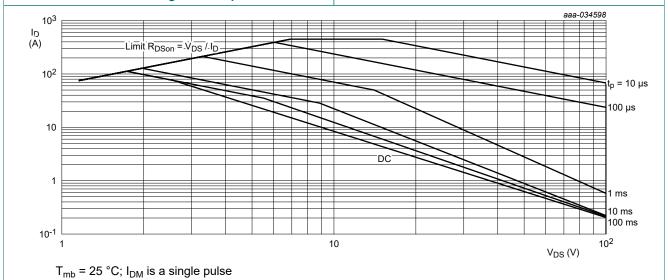
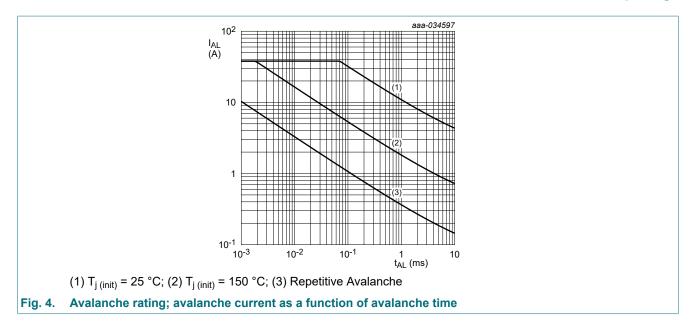


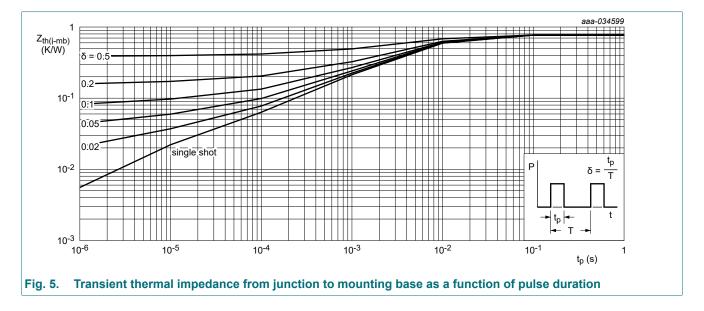
Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.69	0.77	K/W
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance from	Fig. 6	-	42	-	K/W
	Fig. 7	-	85	-	K/W	



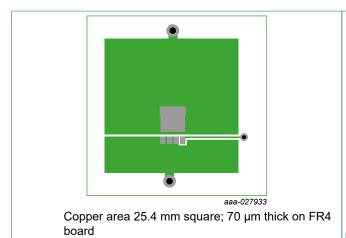
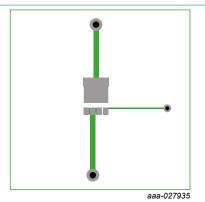


Fig. 6. PCB layout for thermal resistance from junction to ambient



70 µm thick copper on FR4 board

Fig. 7. PCB layout with minimum footprint for thermal resistance from junction to ambient

### 9. Characteristics

#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics		<u> </u>	_		<b>-</b>
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	100	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 11$	2	3	4	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	-	1.7	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	3.4	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-7.6	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.04	1	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	4	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12	-	5	6.9	mΩ
		V <sub>GS</sub> = 7 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	5.8	10.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 13	-	7.8	11	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 13	-	11	15.7	mΩ
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.85	1.7	3.42	Ω
Dynamic cha	racteristics			'		
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	25.4	51	76	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 ^{\circ}\text{C}$	-	25.6	-	nC

Symbol	Parameter	Conditions	Mi	in	Тур	Max	Unit
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V;	9		15	21	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	T <sub>j</sub> = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-		9.6	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-		5.5	-	nC
Q <sub>GD</sub>	gate-drain charge		3.:	2	11	25	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; T <sub>j</sub> = 25 °C; Fig. 14; Fig. 15	-		4.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16$	20	55	3426	4797	pF
C <sub>oss</sub>	output capacitance		49	16	827	1323	pF
C <sub>rss</sub>	reverse transfer capacitance		2.3	3	23	60	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$	-		14	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-		16	-	ns
$t_{d(off)}$	turn-off delay time		-		33	-	ns
t <sub>f</sub>	fall time	1	-		19	-	ns
Source-drai	in diode				'	1	-
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-		0.83	1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-		31	-	ns
Qr	recovered charge	$V_{DS} = 50 \text{ V; } T_j = 25 \text{ °C; } Fig. 18$	-		21	-	nC

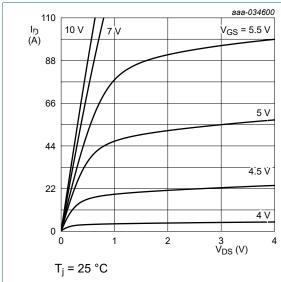


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

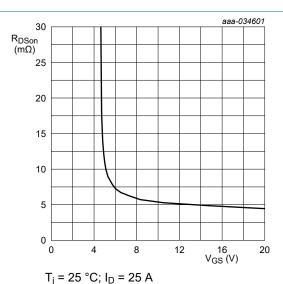


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

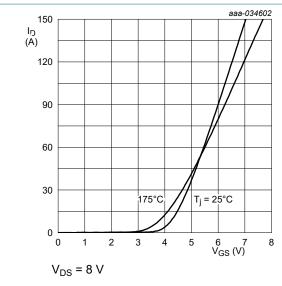


Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values

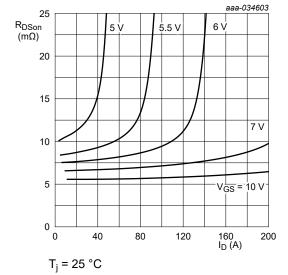


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

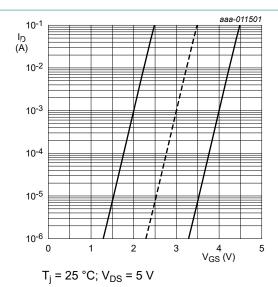


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

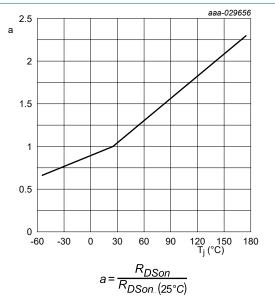


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

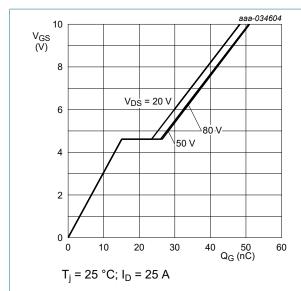


Fig. 14. Gate-source voltage as a function of gate charge; typical values

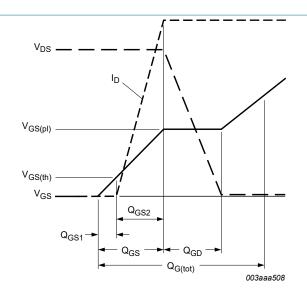


Fig. 15. Gate charge waveform definitions

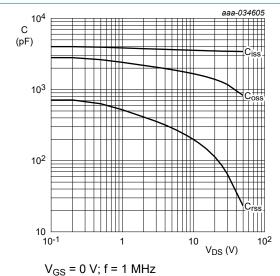
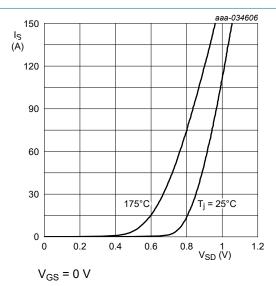


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source-drain (diode forward) current as a as a function of drain-source voltage; typical values



function of source-drain (diode forward) voltage; typical values

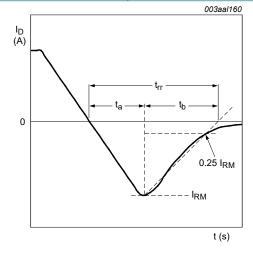
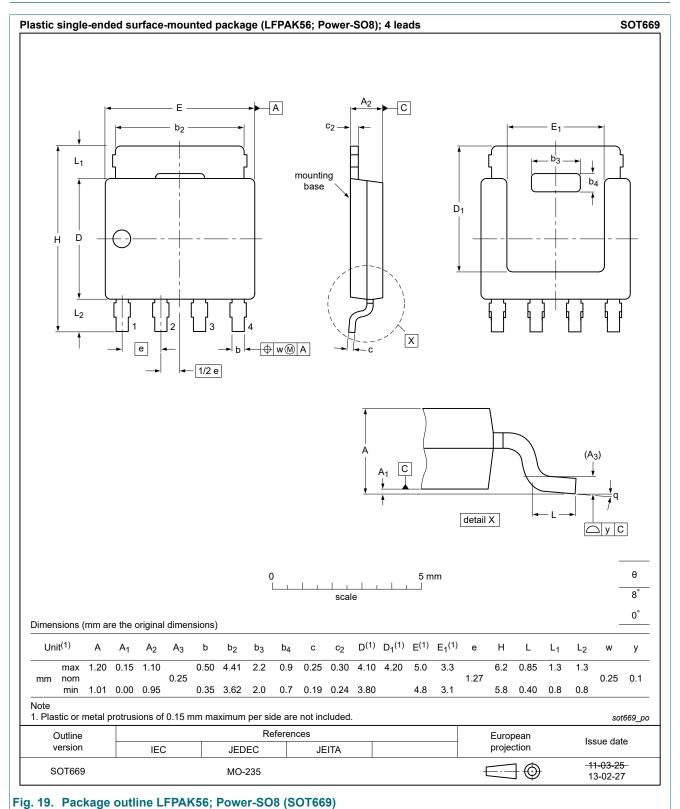
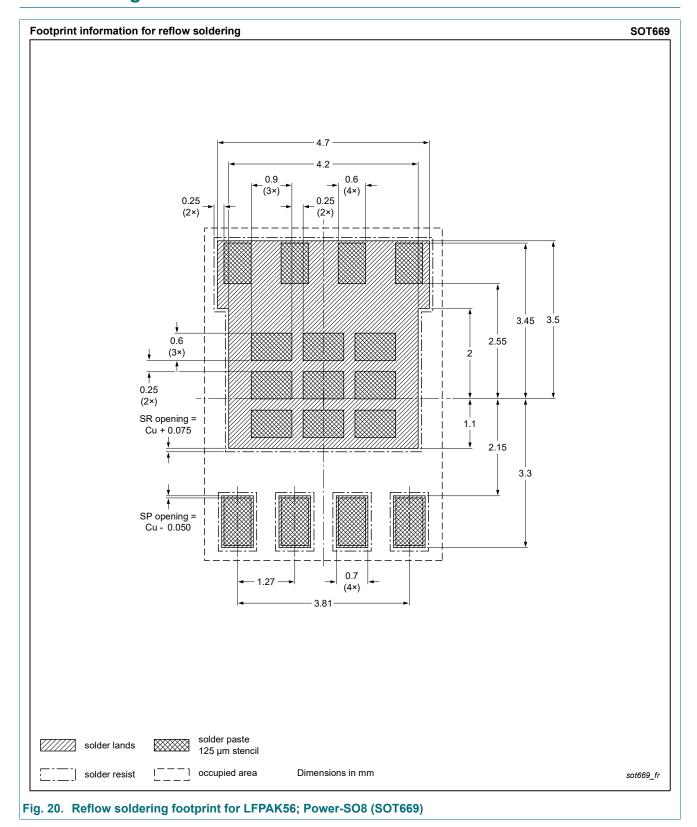


Fig. 18. Reverse recovery timing definition

# 10. Package outline



# 11. Soldering



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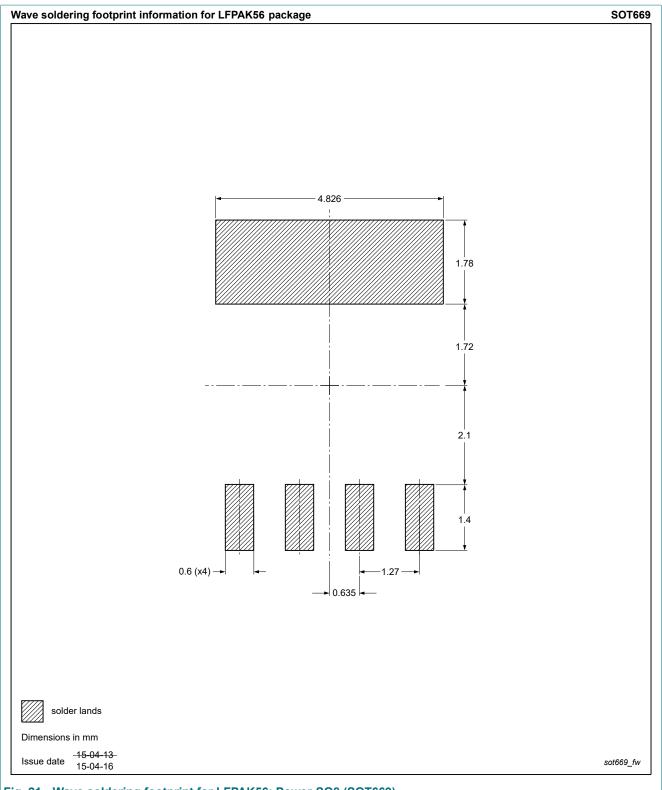


Fig. 21. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

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Document status [1][2]	Product status [3]	Definition
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